TECHNICAL DATA DATA SHEET 4146, REV. B

LOW RDS HERMETIC POWER MOSFET - N-CHANNEL

FEATURES:

- 100 Volt, 0.011 Ohm, 90A MOSFET for Glidcop version
- Isolated Hermetic Metal Package
- Ultra Low R_{DS (on)}
- Ceramic Seals with Glidcop leads (SHDCG225701)

MAXIMUM RATINGS

ALL RATINGS ARE AT $T_c = 25^{\circ}$ C UNLESS OTHERWISE SPECIFIED.

RATING	SYMBOL	MIN.	TYP.	MAX.	UNITS
GATE TO SOURCE VOLTAGE	V_{GS}	-	-	±20	Volts
ON-STATE DRAIN CURRENT	I _{D25}	-	-	55*	Amps
PULSED DRAIN CURRENT	I_{DM}	ı	-	240	Amps
OPERATING AND STORAGE TEMPERATURE	T _J /T _{STG}	-55	-	+150	°C
TOTAL DEVICE DISSIPATION	P_{D}	-	-	210	Watts
THERMAL RESISTANCE, JUNCTION TO CASE	$R_{ heta JC}$	-	-	0.6	°C/W

Note: * current limited by package; die rating is 90A

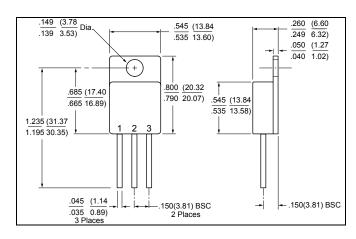
ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNITS
DRAIN TO SOURCE BREAKDOWN VOLTAGE	BV _{DSS}	100	-	-	Volts
$V_{GS} = 0V, I_{D} = 250\mu A$					
STATIC DRAIN TO SOURCE ON STATE RESISTANCE	R _{DS(ON)}				Ω
$V_{GS} = 10V, I_D = 30A$	Glidcop	-	0.011	0.013	
	Version				
STATIC DRAIN TO SOURCE ON STATE RESISTANCE	R _{DS(ON)}		0.040	0.045	Ω
$V_{GS} = 10V, I_D = 30A$	Standard	-	0.013	0.015	
	Version			4	\ / a 4 a
GATE THRESHOLD VOLTAGE $V_{DS} = V_{GS}$, $I_D = 250\mu A$	$V_{GS(th)}$	2	-	4	Volts
FORWARD TRANSCONDUCTANCE	g _{fs}	25	-	-	S(1/Ω)
V_{DS} = 15V, I_{D} = 30A ZERO GATE VOLTAGE DRAIN CURRENT					
				1	^
$V_{DS} = 0.8 \text{ x Max. rating}, V_{GS} = 0V, T_{J} = 25^{\circ}C$	I _{DSS}	_	_	50	μΑ
$T_J = 125$ °C GATE TO SOURCE LEAKAGE FORWARD $V_{GS} = 20$ V				100	nA
GATE TO SOURCE LEAKAGE FORWARD $V_{GS} = 20V$ GATE TO SOURCE LEAKAGE REVERSE $V_{GS} = -20V$		-	-	-100	IIA
TURN ON DELAY TIME $V_{DD} = 50V$	t _{d(ON)}	_	20	30	
RISE TIME I _D = 55A	t _a (ON)		110	170	nsec
	,				
TURN OFF DELAY TIME V _{GS} =10V	$t_{d(OFF)}$		65	100	
FALL TIME $R_G = 2.5\Omega$			100	150	
DIODE FORWARD VOLTAGE $I_F = 30A$, $V_{GS} = 0V$		-	1.0	1.2	Volts
Pulse test, $t \le 300 \mu s$, duty cycle d $\le 2 \%$					
REVERSE RECOVERY TIME $T_J = 25^{\circ}C$,					
$I_F = 30A$, $V_R = 100V$	' t _{rr}	-	70	140	nsec
di/dt = 100A/μsec					
INPUT CAPACITANCE $V_{GS} = 0 V$,	.00	-	8700	-	
OUTPUT CAPACITANCE $V_{DS} = 25 \text{ V},$	000		740		pF
REVERSE TRANSFER CAPACITANCE f = 1.0MHz	C _{rss}		450		

SENSITRON

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MECHANICAL DIMENSIONS: in Inches / mm



TO-254

DEVICE TYPE	PIN-1	PIN-2	PIN-3
N-CHANNEL MOSFET TO-254 PACKAGE	DRAIN	SOURCE	GATE

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